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Sub	stitute for form 1449A/PTO	,		Complete if Known		
				Application Number	Not Yet Assigned	
IN.	IFORMATION	N DI	SCLOSURE	Filing Date		
S	TATEMENT	BY A	APPLICANT	First Named Inventor	Leonard Forbes	
				Group Art Unit	2826	
	(use as many sh	eels as	necessary)	Examiner Name	Not Yet Assigned	
Sheet	1	of	2	Attorney Docket Number	M4065.0381/P381-A	

	Cite No.1	U.S. Patent Document Number Kind Code ² (7 known)		Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*		Office ³	Number ⁴	Kind Code ⁵ (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Where Relevant Passages or Relevant Figures Appear	T⁵
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Signature 1. M. Thomas		15/2 /08 /05
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that Issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁴Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Su	sbstitute for form 1449A/PT	0		Complete if Known		
				Application Number Not Yet Assigned		
	NFORMATIO	N DIS	CLOSURE	Filing Date		
5	STATEMENT	BY AF	PPLICANT	First Named Inventor	Leonard Forbes	
				Group Art Unit	N/A	
	(use as many sl	heets as ne	ecessary)	Examiner Name	Not Yet Assigned	
Sheet	2	of	2	Attorney Docket Number	M4065.0381/P381	

<u></u>		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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Examiner T. M. Thomas	Date Considered 06/08/05
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